UN1596

Preliminary

NPN SILICON TRANSISTOR

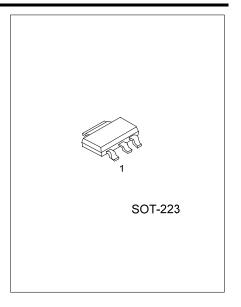
NPN SILICON PLANAR MEDIUM POWER HIGH GAIN TRANSISTOR

■ DESCRIPTION

The UTC **UN1596** are series of NPN silicon planar transistor, which has gain of 500 at I_C =100mA.It can be used in such applications: battery powered circuit and darlington replacement.

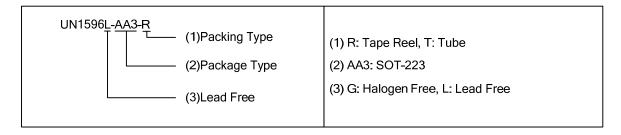
■ FEATURES

- * Gain :500 @ I_C=100mA
- * Low saturation voltage



■ ORDERING INFORMATION

Ordering Number		Dookogo	Pin Assignment			Doelsing	
Lead Free	Halogen Free	Package	1	2	3	Packing	
UN1596L-AA3-R	UN1596G-AA3-R	SOT-223	В	С	E	Tape Reel	



<u>www.unisonic.com.tw</u> 1 of 2

ABSOLUTE MAXIMUM RATINGS

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Base Voltage		V_{CBO}	180	V
Collector-Emitter Voltage		$V_{\sf CEO}$	180	V
Emitter-Base Voltage		V_{EBO}	5	V
Collector Current		Ic	0.5	Α
Peak Pulse Current		I _{CM}	1	Α
Collector Power dissipation	T _A =25°C	Pc	2	W
Junction Temperature		T_J	+150	°C
Storage Temperature		T_{STG}	− 55 ~ + 150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (T_A=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT		
Collector-Base Breakdown Voltage	BV _{CBO}	I _C =100μA	180			٧		
Collector-Emitter Breakdown Voltage	BV _{CEO} I _C =10mA		180			V		
Emitter-Base Breakdown Voltage	BV _{EBO} I _E =100μA		5			V		
Base-Emitter Turn-On Voltage	$V_{BE(ON)}$	I _C =200mA, V _{CE} =5V			0.9	V		
Collector Cutoff Current	I_{CBO}	V _{CB} =140V			100	nΑ		
Emitter Cutoff Current	I _{EBO}	V _{EB} =4V			100	nΑ		
ON CHARACTERISTICS								
		I _C =50mA, I _B =0.5mA		0.2				
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	I _C =100mA, I _B =2mA		0.2		V		
		I _C =250mA, I _B =5mA		0.25				
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	I _C =20mA, I _B =5mA			0.9	V		
DO C I T for Bullin	h _{FE}	I _C =100mA, V _{CE} =5V	500					
DC Current Transfer Ratio		I _C =200mA, V _{CE} =5V	150					
SMALL-SIGNAL CHARACTERISTICS	S							
Transition Frequency	f _T	I _C =50mA, V _{CE} =5V, f=50MHz	70			MHz		
Input Capacitance	Cı	V _{EB} =0.5V, f=1MHz			200	рF		
Output Capacitance	Co	V _{CB} =10V, f=1MHz			6	pF		
Outilability Times	t _{ON}	I _C =100mA, I _{B1} =10mA		80				
Switching Times	t _{OFF}	I _{B2} =10mA, V _{CC} =50V		4400		ns		

Note: Pulse width=300 μ s. Duty cycle \leq 2%

UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice.